

**Amendments to the Specification:**

Please insert the following at page 1, line 5:

By Inventors:

Chok W. Ho

Kuo-Lung Tang

Chung-Ju Lee

Please replace the paragraph located on page 1, lines 7-11, with the following amended paragraph:

This application is ~~also~~ related to the commonly assigned U.S. Patent Application No.: 09/782,185 (Attorney Docket No. LAM1P147/P0675) entitled UNIQUE PROCESS CHEMISTRY FOR ETCHING ORGANIC LOW-K MATERIALS, by Helen H. Zhu, filed ~~concurrently herewith~~ February 12, 2001 and incorporated herein by reference.

Please replace the paragraph located on page 1, lines 12-17, with the following amended paragraph:

This application is also related to the commonly assigned U.S. Patent Application No.: 09/782,678 (Attorney Docket No.: LAM1P149/P0685) entitled POST-ETCH PHOTORESIST STRIP WITH O<sub>2</sub> AND NH<sub>3</sub> FOR ORGANOSILICATE GLASS LOW-K DIELECTRIC ETCH APPLICATIONS, by Rao V. Annapragada et al., filed ~~concurrently herewith~~ February 12, 2001 and incorporated herein by reference.

Please replace the paragraph located on page 1, lines 18-23, with the following amended paragraph:

This application is also related to the commonly assigned U.S. Patent Application No.: 09/782,437 (now Patent No. 6,620,733 B2, issued September 16, 2003) (Attorney Docket No. LAM1P153/P0693) entitled USE OF HYDROCARBON ADDITION FOR THE ELIMINATION OF MICROMASKING DURING ETCHING OF ORGANIC LOW-K DIELECTRICS, by Chok W. Ho, filed ~~concurrently herewith~~ February 12, 2001 and incorporated herein by reference.

Please insert the following paragraph at page 1, line 24:

This is a Divisional application of co-pending prior U.S. Application No. 09/782,446 (Atty. Dkt. No. LAM1P152/P0692), entitled "USE OF AMMONIA FOR ETCHING ORGANIC LOW-K DIELECTRICS", filed on February 12, 2001, which is incorporated herein by reference and from which priority under 35 U.S.C. § 120 is claimed.